

Session Code [09] MoJ3

Session Title	Power / Oxide Semiconductor Materials and Devices
Date and Time	Monday, October 4, 2021 / 15:30-16:40
Session Room	Room J (401)
Session Chair(s)	Daesu Lee (POSTECH, Korea)

[[09] MoJ3-1]**[Online] 15:30-15:45****Characterization of X-Ray Radiation Hardness of Diamond Schottky Barrier Diodes up to 10 MGy**

Phongsaphak Sittimart, Shinya Ohmagari, Tomoki Iwao, Hitoshi Umezawa (*Nat'l Inst. of Advanced Industrial Sci. and Tech., Japan*), Katoro Ishiji (*Kyushu Synchrotron Light Research Center, Japan*), and Tsuyoshi Yoshitake (*Kyushu Univ., Japan*)

[[09] MoJ3-2]**[Online] 15:45-16:00****Zn-Doped p-Type β -Ga₂O₃: Ultra-High Critical Electric Field**

Ekaterine Chikoidze (*Univ. Paris-Saclay, France and CNRS, France*), Tamar Tchelidze (*Ivane Javakhishvili Tbilisi State Univ., Georgia*), Corinne Sartel, Zeyu Chi (*Univ. Paris-Saclay, France and CNRS, France*), Riad Kabouche (*IEMN, CNRS, France*), Ismail Madaci (*Univ. Paris-Saclay, France and CNRS, France*), Carles Rubio (*ICN2, Spain*), Hagar Mohamed, Vincent Sallet (*Univ. Paris-Saclay, France and CNRS, France*), Farid Medjdoub (*IEMN, CNRS, France*), and Yves Dumont (*Univ. Paris-Saclay, France and CNRS, France*)

[[09] MoJ3-3]**16:00-16:15****Advanced Thermal Interface Material with High Thermal Conductivity for High Power Devices**

MiKyeong Choi (*Amkor Tech. Inc., Korea and Sungkyunkwan Univ., Korea*), HyunHye Jung, DongJoo Park, JinYoung Khim (*Amkor Tech. Inc., Korea*), and SeungBoo Jung (*Sungkyunkwan Univ., Korea*)

[[09] MoJ3-4] Invited Talk**[Online] 16:15-16:40****Enhancing Dielectric Constant of ZnO by Acceptor-Donor Co-Doping**

Chi-Chung Francis Ling, Dong Huang, Yingli Shi (*The Univ. of Hong Kong, Hong Kong*), Shengqiang Zhou (*Helmholtz-Zentrum Dresden-Rossendorf, Germany*), and Andrej Kuznetsov (*Univ. of Oslo, Norway*)